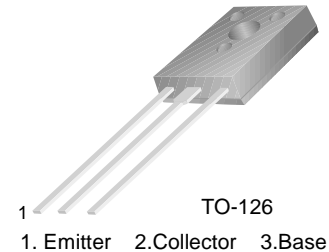


MJE200

Feature

- Low Collector-Emitter Saturation Voltage
- High Current Gain Bandwidth Product : $f_T=65\text{MHz}$ @ $I_C=100\text{mA}$ (Min.)
- Complement to MJE210



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|--|------------|------------------|
| V_{CBO} | Collector-Base Voltage | 40 | V |
| V_{CEO} | Collector-Emitter Voltage | 25 | V |
| V_{EBO} | Emitter- Base Voltage | 8 | V |
| I_C | Collector Current | 5 | A |
| P_C | Collector Dissipation ($T_C=25^\circ\text{C}$) | 15 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | - 65 ~ 150 | $^\circ\text{C}$ |

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|---------------|--------------------------------------|---|----------------|--------------------|---------------------|
| BV_{CEO} | Collector-Emitter Breakdown Voltage | $I_C=10\text{mA}$, $I_B=0$ | 25 | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB}=40\text{V}$, $I_E=0$ $V_{CB}=40\text{V}$, $I_E=0$ @ $T_J=125^\circ\text{C}$ | | 100 100 | nA μA |
| I_{EBO} | Emitter Cut-off Current | $V_{BE}=8\text{V}$, $I_C=0$ | | 100 | nA |
| h_{FE} | DC Current Gain | $V_{CE}=1\text{V}$, $I_C=500\text{mA}$ $V_{CE}=1\text{V}$, $I_C=2\text{A}$ $V_{CE}=2\text{V}$, $I_C=5\text{A}$ | 70 45 10 | 180 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C=500\text{mA}$, $I_B=50\text{mA}$ $I_C=2\text{A}$, $I_C=200\text{mA}$ $I_C=5\text{A}$, $I_B=1\text{A}$ | | 0.3 0.75 1.8 | V V V |
| $V_{BE(sat)}$ | Base- Emitter Saturation Voltage | $I_C=5\text{A}$, $I_B=1\text{A}$ | | 2.5 | V |
| $V_{BE(on)}$ | Base-Emitter ON Voltage | $V_{CE}=1\text{V}$, $I_C=2\text{A}$ | | 1.6 | V |
| f_T | Current Gain Bandwidth Product | $V_{CE}=10\text{V}$, $I_C=100\text{mA}$ | 65 | | MHz |
| C_{ob} | Output Capacitance | $V_{CB}=10\text{V}$, $I_E=0$, $f=0.1\text{MHz}$ | | 80 | pF |

Typical Characteristics

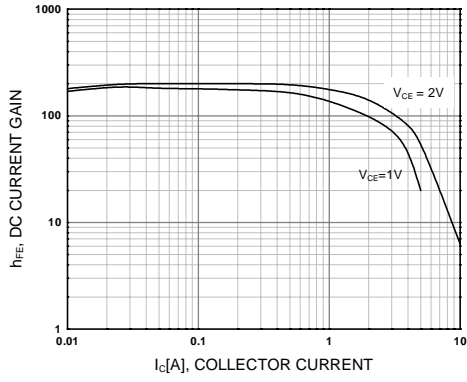


Figure 1. DC current Gain

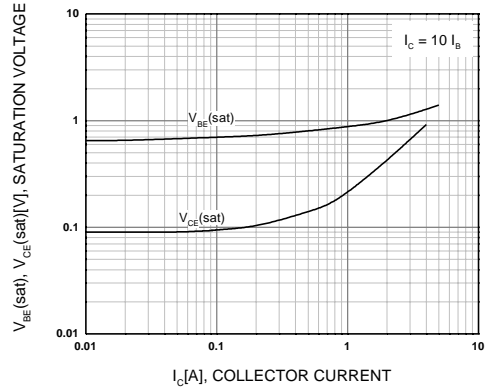


Figure 2. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage

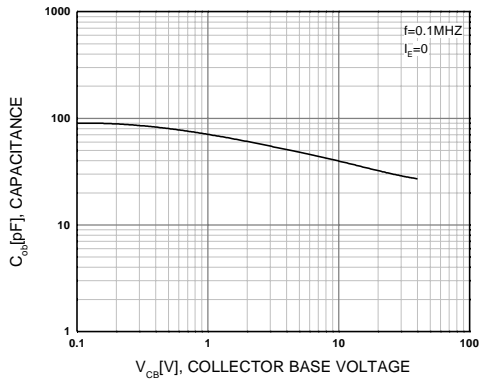


Figure 3. Collector Output Capacitance

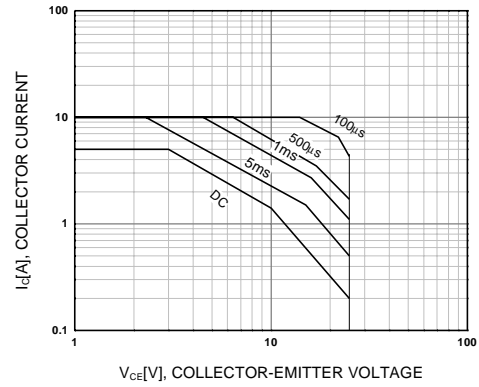


Figure 4. Safe Operating Area

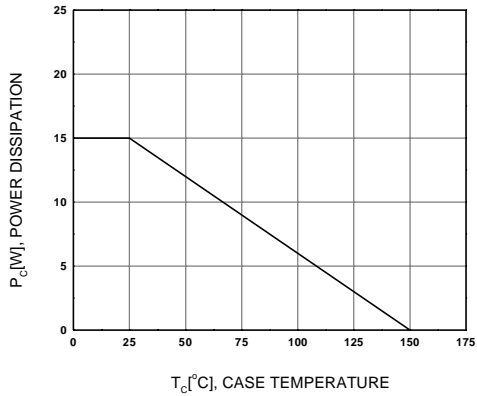
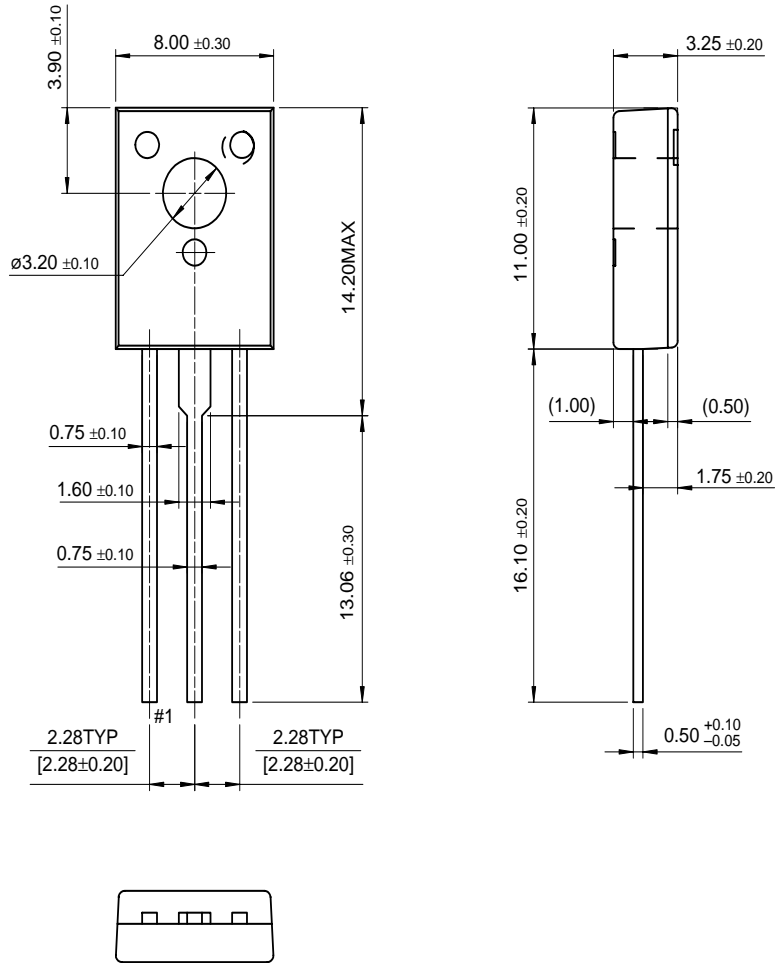


Figure 5. Power Derating

Package Dimensions

TO-126



Dimensions in Millimeters

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